



Product Overview

NSR02F30NXT5G: Schottky Barrier Diode, 200 mA, 30 V

For complete documentation, see the data sheet

Product Description

The Schottky diode is optimized for low forward voltage drop and low leakage current. The DSN2 Dual Silicon no lead package is a chip level package using solderable metal contacts under the package similar to DFN style packages. The DSN style package enables 100 percent utilization of the package area for active silicon offering a significant performance per board area advantage compared to products in plastic molded packages. The low thermal resistance enables designers to meet the challenging task of achieving higher efficiency and meeting reduced space requirements.

Features

- Low Forward Voltage Drop
- High Switching Speed
- High ESD Rating
- Low Reverse Current

Benefits

- Reduces Power Dissipation
- Better Performance
- HBM: 3B MM: C

Applications

- LCD and Keypad Backlighting
- Camera Photo Flash
- Buck and Boost DC-DC Converters

End Products

- Reverse Voltage and Current Protection
- Mobile Handsets
- Notebooks, PCs & PDA
- GPS, MP3 Players

Part Electrical Specifications

Product	Compliance	Status	Configuration	V_{RRM} Min (V)	V_F Max (V)	I_{RM} Max (uA)	$I_{O(rec)}$ Max (A)	I_{FSM} Max (A)	t_{rr} Max (ns)	C_j Max (pF)	Package Type
NSR02F30NXT5G	Pb-free Halide free	Active	Single	30	0.37	7	0.2	4	-	7	DSN-2

For more information please contact your local sales support at www.onsemi.com

Created on: 7/11/2015